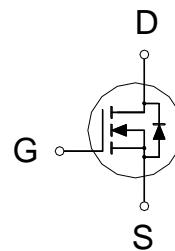


NIKO-SEM
**N-Channel Enhancement Mode
Field Effect Transistor**
PEE50BB
PDFN 3x3P
Halogen-Free & Lead-Free
PRODUCT SUMMARY

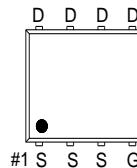
| $V_{(BR)DSS}$ | $R_{DS(on)}$ | I_D |
|---------------|--------------|-------|
| 30V | 1.4mΩ | 138A |

**Features**

- Pb-Free, Halogen Free and RoHS compliant.
- Low $R_{DS(on)}$ to Minimize Conduction Losses.
- Ohmic Region Good $R_{DS(on)}$ Ratio.
- Optimized Gate Charge to Minimize Switching Losses.

Applications

- Protection Circuits Applications.
- Logic/Load Switch Circuits Applications.


G. GATE
D. DRAIN
S. SOURCE

100% UIS Tested
100% Rg Tested
ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

| PARAMETERS/TEST CONDITIONS | | SYMBOL | LIMITS | UNITS |
|--|---------------------------|----------------|------------|-------|
| Drain-Source Voltage | | V_{DS} | 30 | V |
| Gate-Source Voltage | | V_{GS} | ± 20 | V |
| Continuous Drain Current | $T_C = 25^\circ\text{C}$ | I_D | 138 | A |
| | $T_C = 100^\circ\text{C}$ | | 87 | |
| Pulsed Drain Current ¹ | | I_{DM} | 218 | |
| Continuous Drain Current | $T_A = 25^\circ\text{C}$ | I_D | 40 | A |
| | $T_A = 70^\circ\text{C}$ | | 32 | |
| Avalanche Current | | I_{AS} | 47 | |
| Avalanche Energy | $L = 0.1\text{mH}$ | E_{AS} | 110 | mJ |
| Power Dissipation | $T_C = 25^\circ\text{C}$ | P_D | 48 | W |
| | $T_C = 100^\circ\text{C}$ | | 19 | |
| Power Dissipation ³ | $T_A = 25^\circ\text{C}$ | P_D | 4 | W |
| | $T_A = 70^\circ\text{C}$ | | 2.5 | |
| Operating Junction & Storage Temperature Range | | T_j, T_{stg} | -55 to 150 | °C |

NIKO-SEM
**N-Channel Enhancement Mode
Field Effect Transistor**
**PEE50BB
PDFN 3x3P
Halogen-Free & Lead-Free**
THERMAL RESISTANCE RATINGS

| THERMAL RESISTANCE | | SYMBOL | TYPICAL | MAXIMUM | UNITS |
|----------------------------------|--------------|-----------------|---------|---------|--------|
| Junction-to-Ambient ² | $t \leq 10s$ | $R_{\theta JA}$ | | 31 | °C / W |
| Junction-to-Ambient ² | Steady-State | $R_{\theta JA}$ | | 56 | |
| Junction-to-Case | Steady-State | $R_{\theta JC}$ | | 2.6 | |

¹Pulse width limited by maximum junction temperature.²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ C$.³The Power dissipation is based on $R_{\theta JA} t \leq 10s$ value.**ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ C$, Unless Otherwise Noted)**

| PARAMETER | SYMBOL | TEST CONDITIONS | LIMITS | | | UNIT |
|---|---------------|---|--------|------|-----------|-----------|
| | | | MIN | TYP | MAX | |
| STATIC | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS} = 0V, I_D = 250\mu A$ | 30 | | | V |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\mu A$ | 1.3 | 1.6 | 2.3 | |
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0V, V_{GS} = \pm 20V$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 24V, V_{GS} = 0V$ | | | 1 | μA |
| | | $V_{DS} = 20V, V_{GS} = 0V, T_J = 55^\circ C$ | | | 5 | |
| Drain-Source On-State Resistance ¹ | $R_{DS(ON)}$ | $V_{GS} = 4.5V, I_D = 13A$ | | 1.7 | 2.7 | $m\Omega$ |
| | | $V_{GS} = 10V, I_D = 13A$ | | 1 | 1.4 | |
| Forward Transconductance ¹ | g_{fs} | $V_{DS} = 5V, I_D = 13A$ | | 74 | | S |
| DYNAMIC | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$ | | 3018 | | pF |
| Output Capacitance | C_{oss} | | | 1276 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 78 | | |
| Gate Resistance | R_g | $V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$ | | 1.4 | | Ω |
| Total Gate Charge ² | Q_g | $V_{DS} = 15V, V_{GS} = 10V, I_D = 13A$ | | 53 | | nC |
| | | | | 26 | | |
| Gate-Source Charge ² | Q_{gs} | | | 7.2 | | |
| Gate-Drain Charge ² | Q_{gd} | | | 9.5 | | |
| Turn-On Delay Time ² | $t_{d(on)}$ | | | 16 | | |
| Rise Time ² | t_r | | | 62 | | |
| Turn-Off Delay Time ² | $t_{d(off)}$ | $V_{DS} = 15V, I_D \geq 13A, V_{GS} = 10V, R_{GEN} = 6\Omega$ | | 73 | | nS |
| Fall Time ² | t_f | | | 88 | | |

NIKO-SEM**N-Channel Enhancement Mode
Field Effect Transistor****PEE50BB
PDFN 3x3P
Halogen-Free & Lead-Free****SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)**

| | | | | | | |
|------------------------------|-----------------|---|--|----|-----|----|
| Continuous Current | I _S | | | | 36 | A |
| Forward Voltage ¹ | V _{SD} | I _F = 13A, V _{GS} = 0V | | | 1.2 | V |
| Reverse Recovery Time | t _{rr} | I _F = 13A, dI _F /dt = 100A / μS | | 37 | | nS |
| Reverse Recovery Charge | Q _{rr} | | | 29 | | nC |

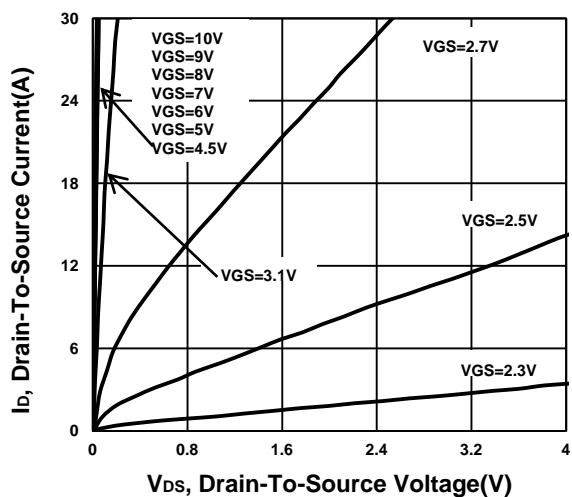
¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.²Independent of operating temperature.

NIKO-SEM

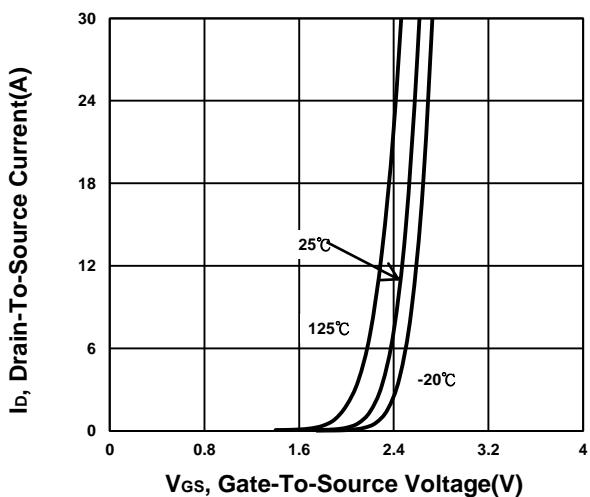
**N-Channel Enhancement Mode
Field Effect Transistor**

PEE50BB
PDFN 3x3P
Halogen-Free & Lead-Free

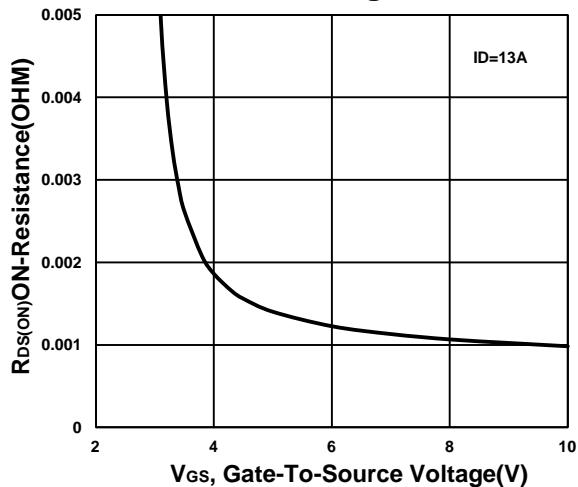
Output Characteristics



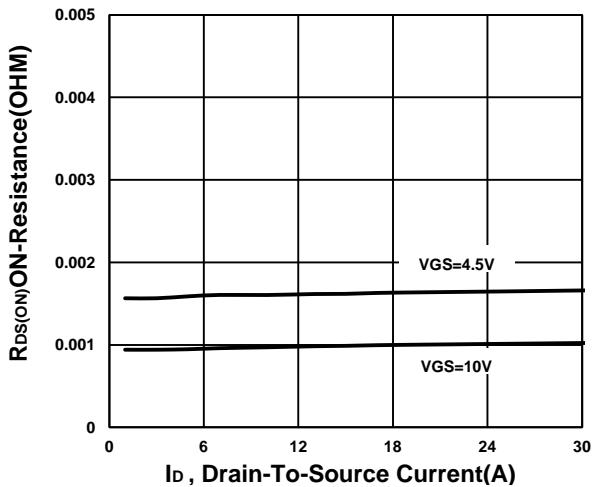
Transfer Characteristics



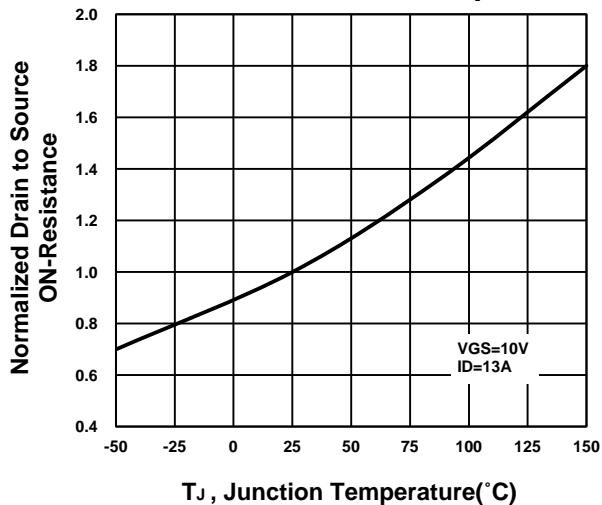
On-Resistance VS Gate-To-Source Voltage



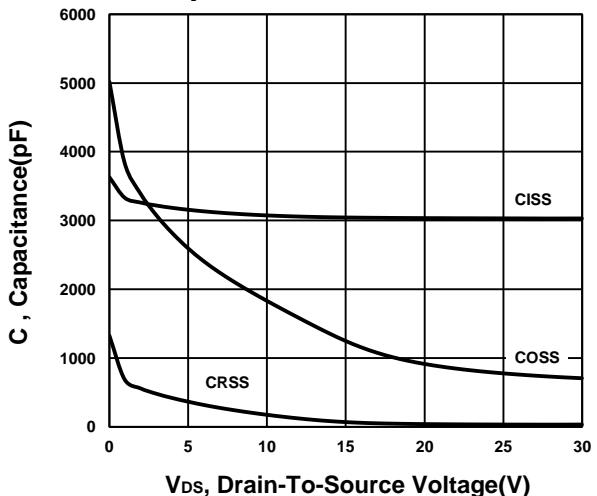
On-Resistance VS Drain Current

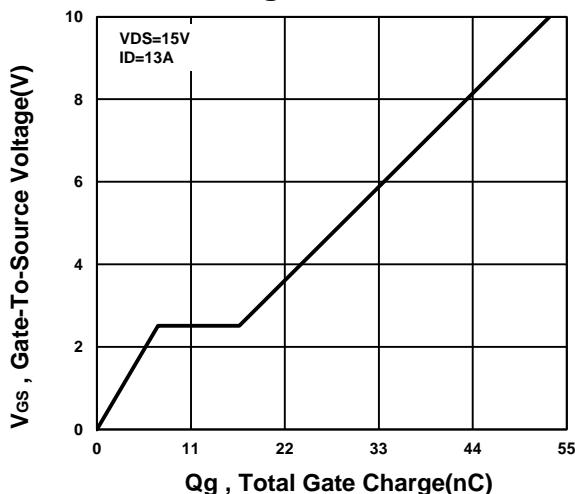
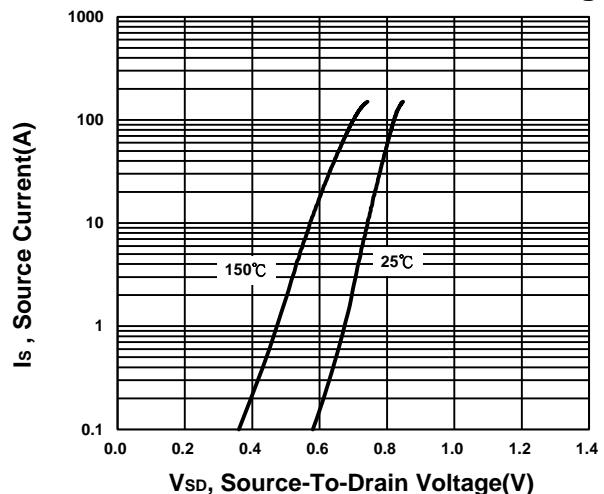
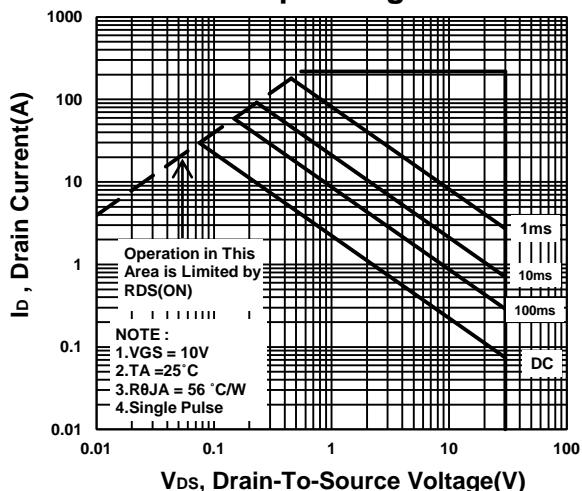
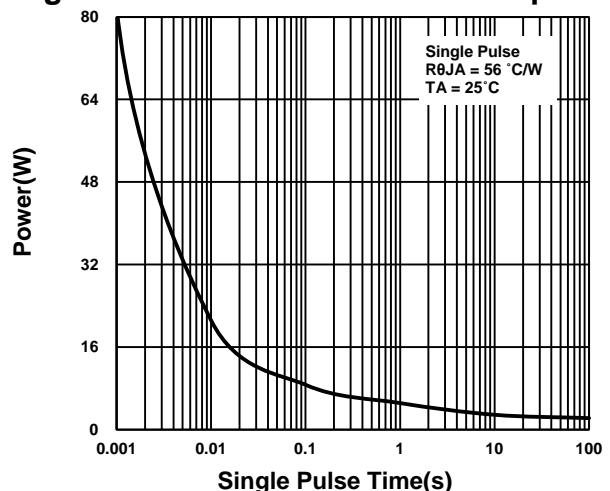
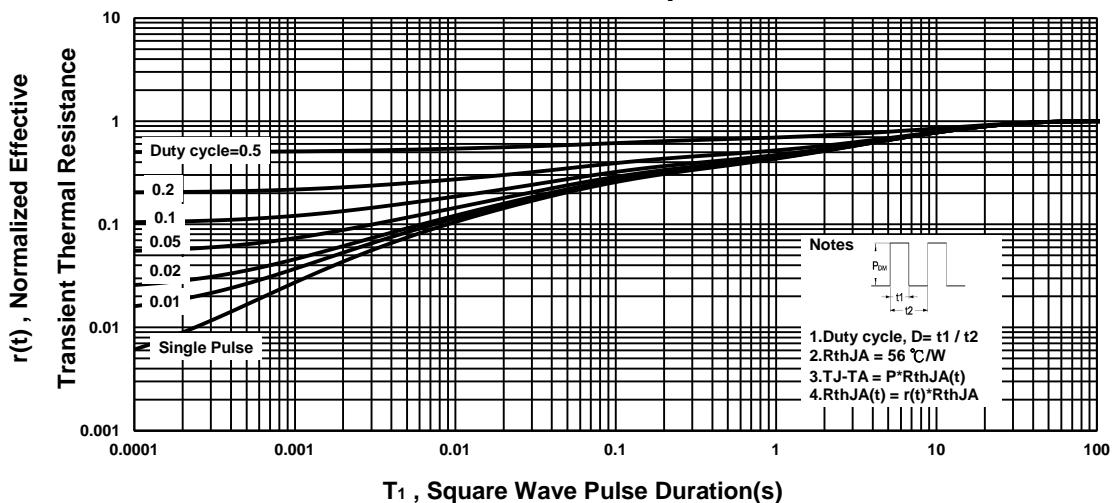


On-Resistance VS Temperature



Capacitance Characteristic



NIKO-SEM**N-Channel Enhancement Mode
Field Effect Transistor****PEE50BB
PDFN 3x3P
Halogen-Free & Lead-Free****Gate charge Characteristics****Source-Drain Diode Forward Voltage****Safe Operating Area****Single Pulse Maximum Power Dissipation****Transient Thermal Response Curve**

NIKO-SEM

**N-Channel Enhancement Mode
Field Effect Transistor**

PEE50BB
PDFN 3x3P
Halogen-Free & Lead-Free

